WHAT IS CLAIMED IS:

1. A semiconductor device comprising a pixel portion with an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon,

wherein an organic resin insulating layer is formed over said insulated gate field effect transistor, and

wherein a storage capacitance is formed of a light shielding layer formed over said organic resin insulating layer, a dielectric layer formed to be in close contact with said light shielding layer, and a light reflecting electrode connected to said insulated gate field effect transistor.

2. A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, said semiconductor device comprising:

an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon over one of said substrates,

wherein an organic resin insulating layer is formed over said insulated gate field effect transistor,

wherein a storage capacitance is formed of a light shielding layer formed over said organic resin insulating layer, a dielectric layer formed to be in close contact with said light shielding layer, and a light reflecting electrode connected to said insulated gate field effect transistor, and

wherein at least one light transmitting conductive film is formed over the other of said substrates.

3. A semiconductor device comprising an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon, and an organic EL component,

wherein an organic resin insulating layer is formed over said insulated gate field effect transistor, and

wherein a storage capacitance is formed of a light shielding layer formed over said organic resin insulating layer, a dielectric layer formed to be in close contact with said light shielding layer, and a light reflecting electrode connected to said insulated gate field effect transistor.

4. A semiconductor device according to any one of claims 1 to 3, wherein an insulating layer made of an inorganic compound is formed between said organic resin insulating layer and said light shielding layer.

5. A semiconductor device according to any one of claims 1 to 3, wherein an insulating layer made of an inorganic compound is formed on a surface of said organic resin insulating layer at a side where said light shielding layer is formed.

6. A semiconductor device according to claim 2, wherein said liquid crystal is thresholdless antiferroelectric mixed liquid crystal.

7. A semiconductor device according to any one of claims 1 to 3, wherein said light shielding layer is made of at least one kind of material selected from the group consisting of aluminum, tantalum, and titanium, and said dielectric layer is an oxide of said material.

8. A semiconductor device according to any one of claims 1 to 3, wherein said semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, a portable book, a digital camera, and a DVD player.

9. A method of fabricating a semiconductor device comprising a pixel portion with an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon, said method comprising the steps of:

forming an organic resin layer over said insulated gate field effect transistor;

forming a light shielding layer over said organic resin layer;

forming a dielectric layer to be in close contact with said light shielding layer; and

forming a light reflecting electrode containing a region overlapping with said light shielding layer through said dielectric layer.

10. A method of fabricating a semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, said method comprising the steps of:

forming an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon over one of said substrates;

forming an organic resin layer over said insulated gate field effect transistor;

forming a light shielding layer over said organic resin layer;

forming a dielectric layer to be in close contact with said light shielding layer;

forming a light reflecting electrode connected to said insulated gate field effect transistor; and

forming a light transmitting conductive film on the other of said substrates,

wherein said light reflecting electrode contains a region overlapping with said light shielding layer through said dielectric layer.

11. A method of fabricating a semiconductor device comprising an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor comprising silicon, and an organic EL component, said method comprising the steps of:

forming an organic resin layer over said insulated gate field effect transistor;

forming a light shielding layer over said organic resin layer;

forming a dielectric layer to be in close contact with said light shielding layer; and

forming a light reflecting electrode connected to said insulated gate field effect transistor,

wherein said light reflecting electrode contains a region overlapping with said light shielding layer through said dielectric layer.

12. A method according to any one of claims 9 to 11, wherein an insulating layer made of an inorganic compound is formed between said organic resin insulating layer and said light shielding layer.

13. A method according to any one of claims 9 to 11, wherein an insulating layer made of an inorganic compound is formed on a surface of said organic resin insulating layer at a side where said light shielding layer is formed.

14. A method according to claim 10, wherein said liquid crystal is thresholdless antiferroelectric mixed liquid crystal.

15. A method according to any one of claims 9 to 11, wherein said light shielding layer is made of at least one kind of material selected from the group consisting of aluminum, tantalum, and titanium, and said dielectric layer is an oxide of said material.

16. A method according to claim 15, wherein said dielectric layer is formed by an anodic oxidation method.

17. A method according to any one of claims 9 to 11, wherein said semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, a portable book, a digital camera, and a DVD player.